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**Haishi et al.**

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(54) **METHOD FOR PRODUCTION OF  
TRANSPARENT CONDUCTIVE FILM**

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See application file for complete search history.

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(57) **ABSTRACT**

A method for producing a transparent conductive film includes heat-treating a transparent conductive film comprising a transparent film substrate and a transparent conductive laminate including a first transparent conductive layer and a second transparent conductive layer, so that the first and the second transparent conductive layers in the transparent conductive film are crystallized, wherein the first transparent conductive layer is a first amorphous layer comprising indium oxide or an indium-based complex oxide having a tetravalent metal element oxide, the second transparent conductive layer is a second amorphous layer comprising an indium-based complex oxide having a tetravalent metal element oxide, wherein each of the first and the second contents of the tetravalent metal element oxide content is expressed by the formula: {the amount of the tetravalent

(Continued)

